

ESD



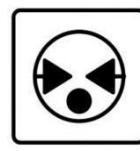
TVS



TSS



MOV



GDT



PLED

TL431B1xxxx-MS

Product specification

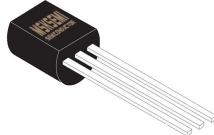
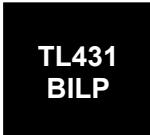
DESCRIPTION

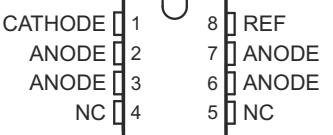
The TL431BIxxxx-MS is a three-terminal adjustable regulator series with a guaranteed thermal stability over applicable temperature ranges. The output voltage may be set to any value between Vref (approximately 2.5 volts) and 40 volts with two external resistors. These devices have a typical dynamic output impedance of 0.2Ω. Active output circuitry provides a very sharp turn-on characteristic, making these devices excellent replacement for zener diodes in many applications.

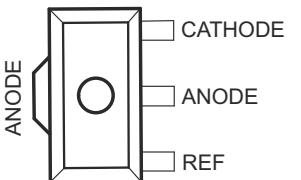
FEATURES

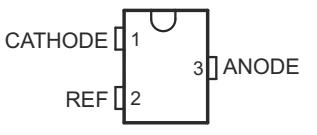
- Programmable Output Voltage to 36V
- Low Dynamic Output Impedance 0.27Ω (Typ)
- Sink Current Capability of 0.1 mA to 100 mA
- Equivalent Full-Range Temperature Coefficient of 50 ppm/°C
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
- Low Output Noise Voltage
- Fast Turn on Respons
- TO-92, SOP-8, SOT-89 or SOT-23 packages

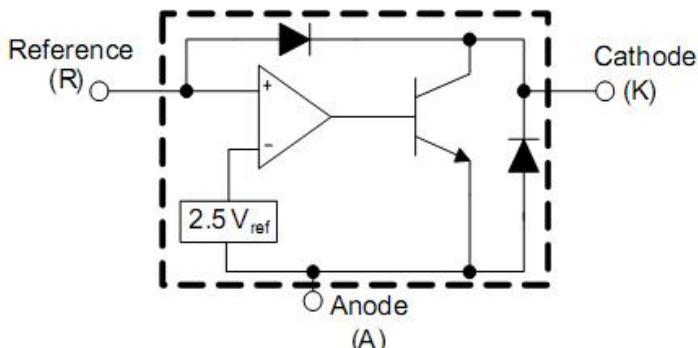
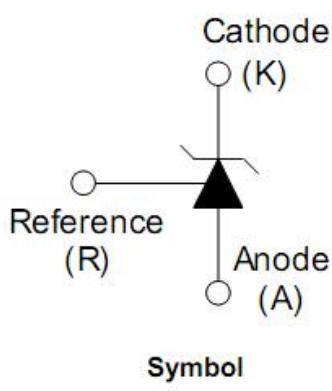
Reference News

TO-92	PIN CONFIGURATION	MARKING
	 CATHODE ANODE REF	 TL431 BILP

SOP-8	PIN CONFIGURATION	MARKING
	 CATHODE 1 8 REF ANODE 2 7 ANODE ANODE 3 6 ANODE NC 4 5 NC NC – No internal connection	 MSKSEMI 431BI MS***

SOT-89	PIN CONFIGURATION	MARKING
	 ANODE CATHODE ANODE REF	 MSKSEMI 431BIPK

SOT-23	PIN CONFIGURATION	MARKING
	 CATHODE 1 REF 2 3 ANODE	 T3F3 MS



ORDER INFORMATION

P/N	PKG	QTY
TL431BILP-MS	TO-92	1000
TL431BIDBZR-MS	SOT-23	3000
TL431BIPK-MS	SOT89-3	1000
TL431BIDR-MS	SOP-8	2500

ABSOLUTE MAXIMUM RATINGS

(Operating temperature range applies unless otherwise specified)

Characteristic	Symbol	Value	Unit
Cathode Voltage	V_{KA}	36	V
Cathode Current Range (Continuous)	I_K	-100 ~ 150	mA
Reference Input Current Range	I_{REF}	-0.05 ~ +10	mA
Power Dissipation at 25°C: TO – 92 Package ($R_{oJA} = 178^\circ\text{C}/\text{W}$) SOT – 23 – 3 Package ($R_{oJA} = 625^\circ\text{C}/\text{W}$)	P_D	0.7 0.2	W W
Junction Temperature Range	T_J	-40 ~ 85	°C
Storage Temperature Range	T_{stg}	-65 ~ +150	°C

RECOMMENDED OPERATING CONDITIONS

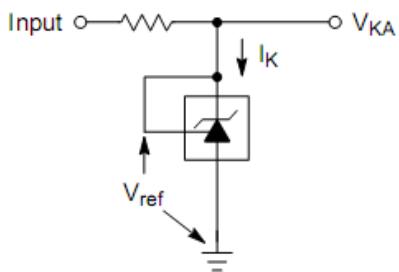
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Cathode Voltage	V_{KA}		V_{REF}		36	V
Cathode Current	I_K		0.5		100	mA

ELECTRICAL CHARACTERISTICS

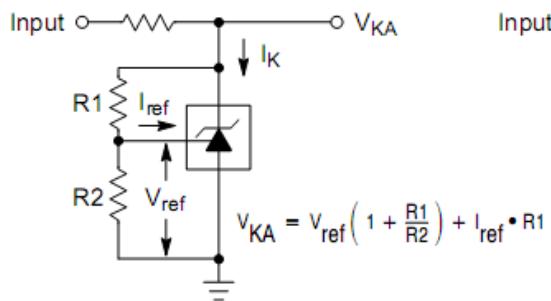
($T_a = 25^\circ\text{C}$, $V_{KA} = V_{REF}$, $I_K = 10\text{mA}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Reference Input Voltage	V_{REF}	$V_{KA} = V_{REF}$, $I_K = 10\text{mA}$	2.483	2.495	2.507	V
Deviation of Reference Input Voltage Over Full Temperature Range	$V_{REF(dev)}$	$T_{min} \leq T_a \leq T_{max}$		3	17	mV
Ratio of Change in Reference Input Voltage to the Change in Cathode Voltage	$\Delta V_{REF}/\Delta V_{KA}$	$\Delta V_{KA} = 10\text{V}-V_{REF}$ $\Delta V_{KA} = 36\text{V}-10\text{V}$	-0.4 -0.4	0.0 0.0	2.7 2.0	mV/V
Reference Input Current	I_{REF}	$R_1 = 10\text{K}\Omega$, $R_2 = \infty$		1.8	4	μA
Deviation of Reference Input Current Over Full Temperature Range	$I_{REF(dev)}$	$R_1 = 10\text{K}\Omega$, $R_2 = \infty$		0.4	1.2	μA
Minimum Cathode Current for Regulation	$I_{K(min)}$			0.25	0.5	mA
Off-State Cathode Current	$I_{K(off)}$	$V_{KA} = 40\text{ V}$, $V_{REF} = 0$		0.17	0.9	μA
Dynamic Impedance	Z_{KA}	$I_K = 1\text{mA}$ 100 mA , $f \leq 1.0\text{KHz}$		0.27	0.5	Ω

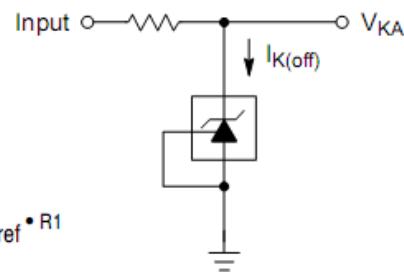
TEST CIRCUITS



Test Circuit
for $V_{KA} = V_{ref}$

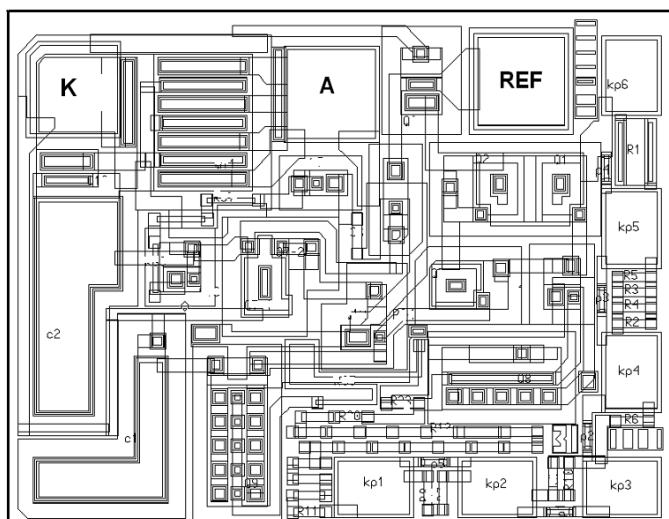


Test Circuit
for $V_{KA} > V_{ref}$



Test Circuit
for $I_{K(off)}$

PAD LAYOUT



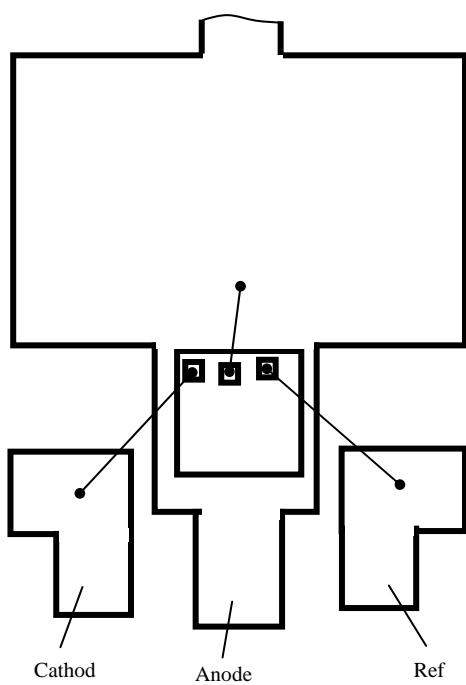
PHISICAL CHARACTERISTICS:

Wafer Diameter.....100 \pm 0.5mm
Wafer Thickness..... 260 \pm 20 μm
Die size.....0.76 x 0.60 mm²
Scribe Width.....60 μm
Pad Size86 x 86 μm
Passivation.....PECVD
Backside metallizationwithout metallization

PAD LOCATION

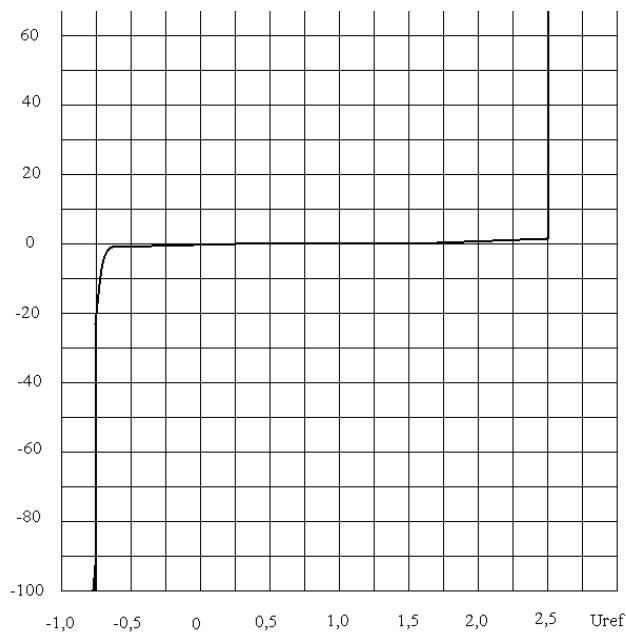
Pad Name	Description	X	Y
K	Cathode	56	445
A	Anode	328	440
R	Reference	528	453

BONDING DIAGRAM

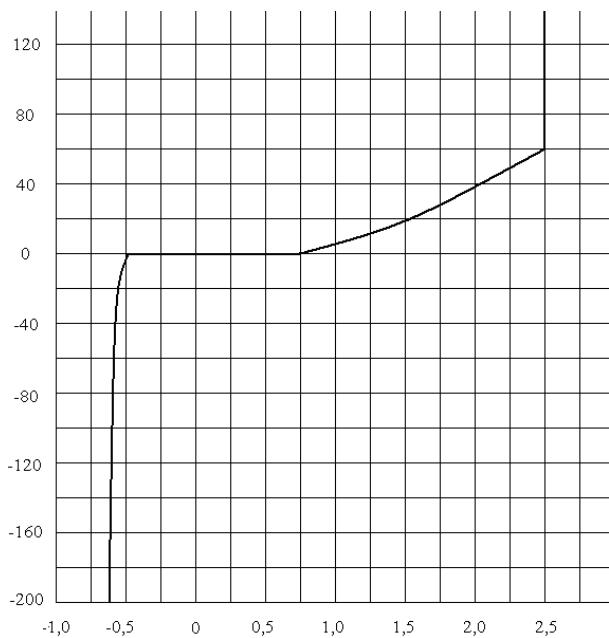


TYPICAL PERFORMANCE CHARACTERISTICS

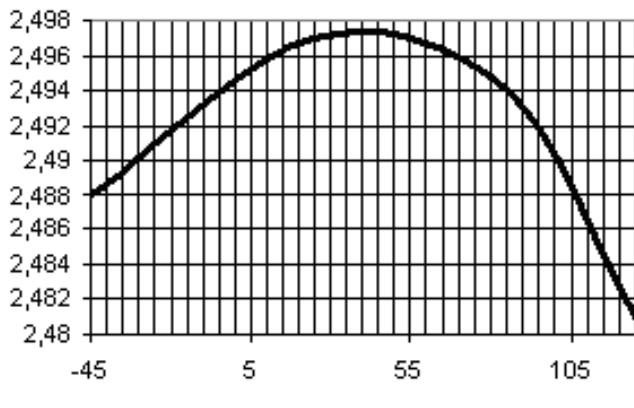
**Cathode Current I_k (mA)
vs. Cathode Voltage U_k (V)**



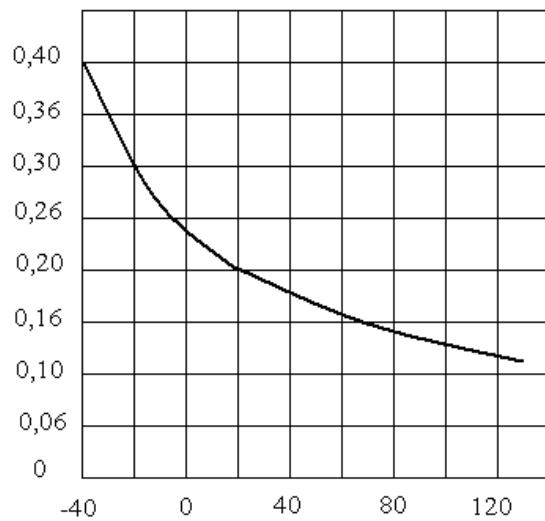
**Cathode Current I_k (uA)
vs. Cathode Voltage U_k (V)**



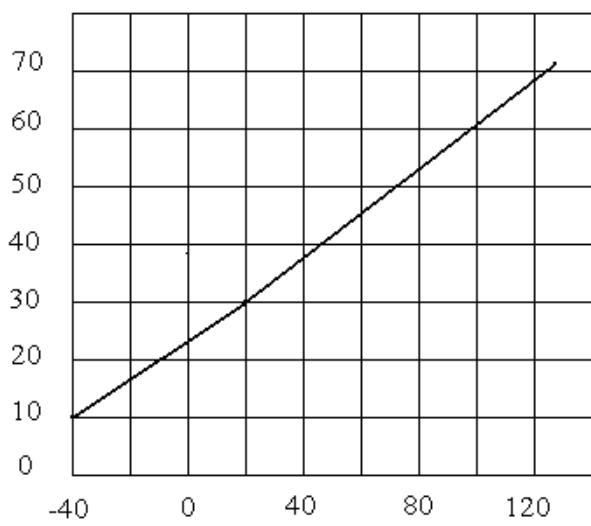
**Reference Voltage U_{ref} (V)
vs. Junction Temperature T_j (°C)
 $I_k=10\text{mA}$**



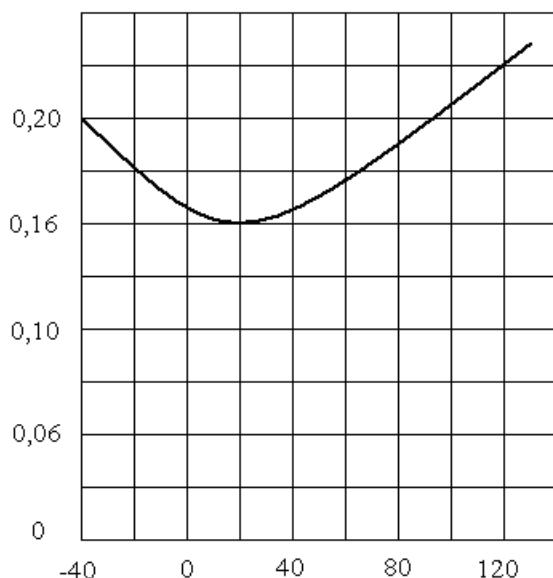
**Reference Input Current I_{ref} (uA)
vs. Junction Temperature T_j (°C)
 $I_k=10\text{mA}$**



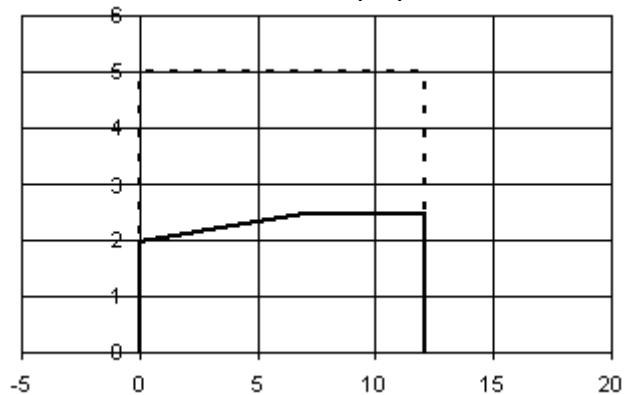
Off-State Cathode Current I_{koff} (uA)
vs. Junction Temperature T_j (°C)
 $U_{ka}=36V$

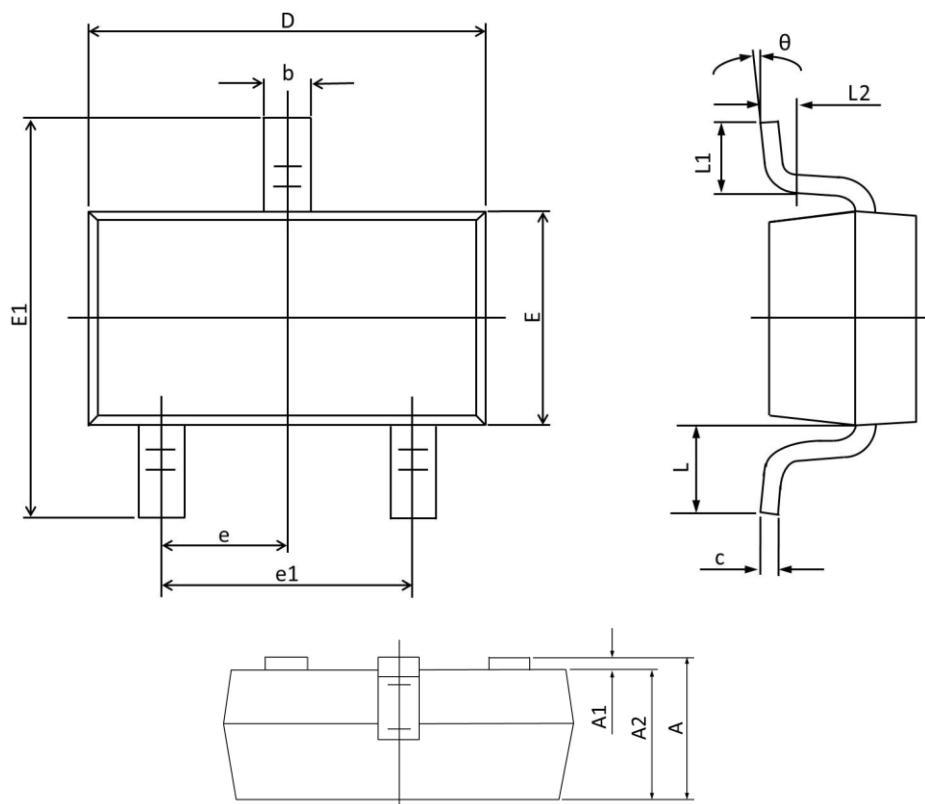


Dynamic Impedance Z_{ka} (Ohm)
vs. Junction Temperature T_j (°C)
 $I_k = 1\div100$ mA



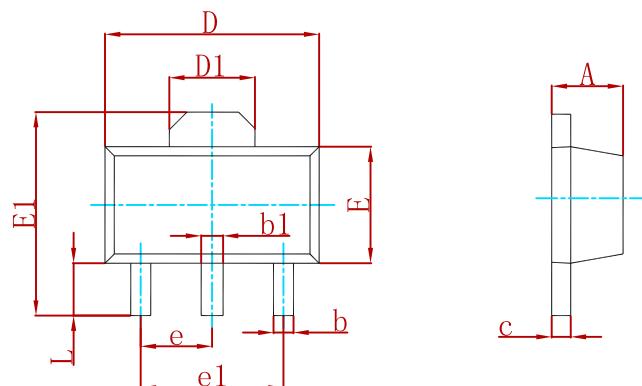
Pulse Response Input and Output Voltage (V)
vs. Time t (uS)



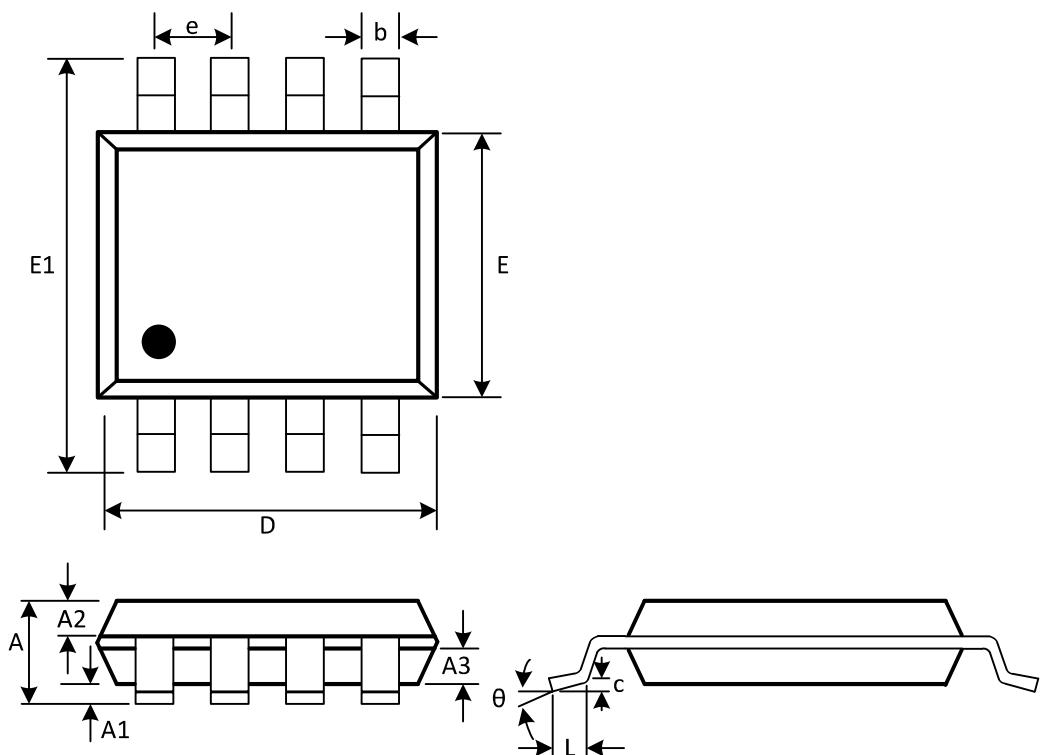
SOT-23 PACKAGE INFORMATION


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Max	Min	Max	Min
A	1.150	0.900	0.045	0.035
A1	0.100	0.000	0.004	0.000
A2	1.050	0.900	0.041	0.035
b	0.500	0.300	0.020	0.012
c	0.150	0.080	0.006	0.003
D	3.000	2.800	0.118	0.110
E	1.400	1.200	0.055	0.047
E1	2.550	2.250	0.100	0.089
e	0.95 TYP.		0.037 TYP.	
e1	2.000	1.800	0.079	0.071
L	0.55 REF.		0.022 REF.	
L1	0.500	0.300	0.020	0.012
L2	0.25 TYP.		0.01 TYP.	
θ	8°	0°	8°	0°

SOT-89 PACKAGE MECHANICAL DATA



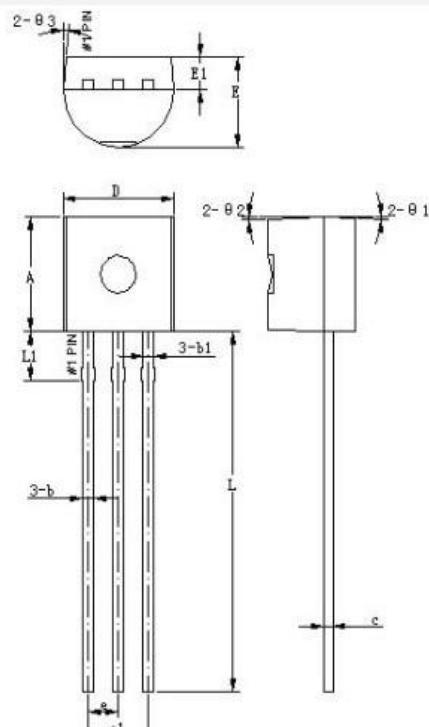
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

SOP-8 PACKAGE MECHANICAL DATA


(Unit: mm)

Symbol	Min	Max
A	1.300	1.600
A1	0.050	0.200
A2	0.550	0.650
A3	0.550	0.650
b	0.356	0.456
c	0.203	0.233
D	4.800	5.000
e	1.270(BSC)	
E	3.800	4.000
E1	5.800	6.200
L	0.400	0.800
θ	0°	8°

TO-92 PACKAGE MECHANICAL DATA



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.5	4.6	4.7
b	0.38	0.46	0.56
b1		0.46	
c	0.36	0.38	0.51
D	4.5	4.6	4.7
E	3.45	3.6	3.75
E1	1.2	1.3	1.4
e		1.27	
e1		2.54	
L	13.5	14.5	15.3
L1		1.96	
b1		2*	
b2		2*	
b3		5*	

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